PROCESS BATCH SHEET (Al DC Sputter Deposition) Issue 4 **Pg_____of_____**

ENSC Batch No.______________________**Wafers Started**_______________**Date**_________________________
Material_________________**Orientation**______________**Size**_______________**Thickness**_________________
Resistivity____________________________________**Type**____
Wafer Vendor______________________**Vendor Batch #**_______________________**SFU P.O.**______________

Process Step #	Process Conditions	Oper & Wafer #	Comments
			Substrates must be very clean. Perform either an RCA clean or a good organic solvent clean. Either must be followed by a thorough rinse / dry
_____A	**Weigh Substrate (optional)** For thickness calculation.		
_____B	**Load Substrates** Secure to holders in chamber		
_____C	**Rough Pump** Evac chamber to 50 mTorr		
_____D	**High Vacuum Pump** To 3 x 10e-6 Torr or lower		
_____E	**Sputter Clean Source** Example: 500 W*min @ 0.2A in current mode at 3 mTorr Ar pressure		
_____F	**Sputter Deposit Aluminum** Example: About 8000 W*min @ 0.2A at 3 mTorr Ar press, depending on thickness needed.		Example: 8000 W*min will give about 1 micron of Al on a single, stationary wafer.
_____G	**Shut Down Process** Stop process (F1), close Hi Vac valve. Bleed chamber to atmosphere.		
_____H	**Remove Substrates** Open chamber. Remove substrates carefully.		
_____I	**Shut Down System** Turn down per procedures		
_____J	**Inspect Substrates** Visual, weight , thickness, adhesion		